

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCUMENT NO. 282830050PCT		SERIAL NO. 10/584,052	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Stephane POCAS, et al.		FILING DATE June 22, 2006	
				GROUP 2892			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
/E.J./	AA	6 274 892	08-14-01	KUB, Francis J. et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
/E.J./	AL	38 29 906	03-15-90	DE (with English abstract)			NO
/E.J./	AM	43 04 349	08-18-94	DE			NO
	AN						
	AO						
	AP						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
/E.J./	AQ	ZHU, Shiyang et al., "Buried Cobalt Silicide Layer Under Thin Silicon Film Fabricated by Wafer Bonding and Hydrogen-Induced Delamination Techniques", Journal of the Electrochemical Society, Vol. 146, No. 7, pgs. 2712-2716, 1999.					
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						<input type="checkbox"/> Additional References sheet(s) attached	
Examiner		/Eric Jones/				Date Considered 1/6/2009	
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							